

2SK1971

Silicon N Channel MOS FET

REJ03G0990-0200
(Previous: ADE-208-1338)
Rev.2.00
Sep 07, 2005

Application

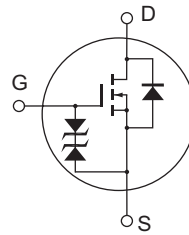
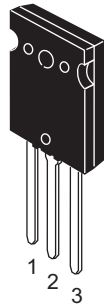
High speed power switching

Features

- Low on-resistance
- High speed switching
- Low drive current
- No secondary breakdown
- Suitable for switching regulator, DC-DC converter, motor control

Outline

RENESAS Package code: PRSS0004ZF-A
(Package name: TO-3PL)



1. Gate
2. Drain
(Flange)
3. Source

Absolute Maximum Ratings

(Ta = 25°C)

Item	Symbol	Ratings	Unit
Drain to source voltage	V_{DSS}	500	V
Gate to source voltage	V_{GSS}	± 30	V
Drain current	I_D	35	A
Drain peak current	$I_{D(pulse)}^{*1}$	140	A
Body to drain diode reverse drain current	I_{DR}	35	A
Channel dissipation	P_{ch}^{*2}	200	W
Channel temperature	T_{ch}	150	°C
Storage temperature	T_{stg}	-55 to +150	°C

Notes: 1. $PW \leq 10 \mu s$, duty cycle $\leq 1 \%$ 2. Value at $T_c = 25^\circ C$

Electrical Characteristics

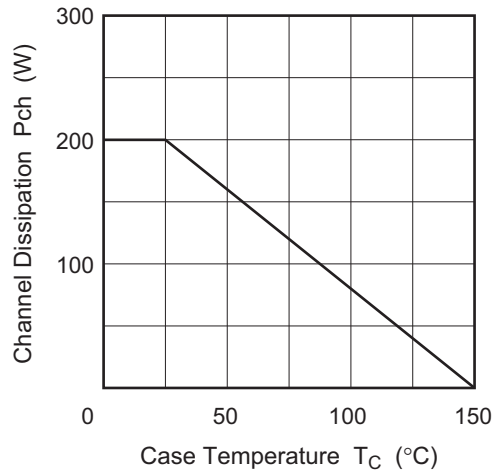
(Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	500	—	—	V	$I_D = 10 \text{ mA}$, $V_{GS} = 0$
Gate to source breakdown voltage	$V_{(BR)GSS}$	± 20	—	—	V	$I_G = \pm 100 \mu A$, $V_{DS} = 0$
Gate to source leak current	I_{GSS}	—	—	± 10	μA	$V_{GS} = \pm 25 \text{ V}$, $V_{DS} = 0$
Zero gate voltage drain current	I_{DSS}	—	—	250	μA	$V_{DS} = 400 \text{ V}$, $V_{GS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	2.0	—	3.0	V	$I_D = 1 \text{ mA}$, $V_{DS} = 10 \text{ V}$
Static drain to source on state resistance	$R_{DS(on)}$	—	0.19	0.23	Ω	$I_D = 18 \text{ A}$, $V_{GS} = 10 \text{ V}^{*3}$
Forward transfer admittance	$ y_{fs} $	16	24	—	S	$I_D = 18 \text{ A}$, $V_{DS} = 10 \text{ V}^{*3}$
Input capacitance	C_{iss}	—	4320	—	pF	$V_{DS} = 10 \text{ V}$, $V_{GS} = 0$, $f = 1 \text{ MHz}$
Output capacitance	C_{oss}	—	1120	—	pF	
Reverse transfer capacitance	C_{rss}	—	130	—	pF	
Turn-on delay time	$t_{d(on)}$	—	50	—	ns	$I_D = 18 \text{ A}$, $V_{GS} = 10 \text{ V}$, $R_L = 1.67 \Omega$
Rise time	t_r	—	170	—	ns	
Turn-off delay time	$t_{d(off)}$	—	320	—	ns	
Fall time	t_f	—	130	—	ns	
Body to drain diode forward voltage	V_{DF}	—	1.1	—	V	$I_F = 35 \text{ A}$, $V_{GS} = 0$
Body to drain diode reverse recovery time	t_{rr}	—	530	—	ns	$I_F = 35 \text{ A}$, $V_{GS} = 0$, $di_F/dt = 100 \text{ A}/\mu s$

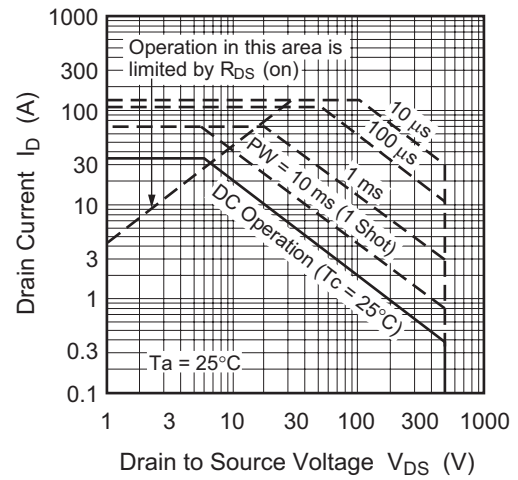
Note: 3. Pulse Test

Main Characteristics

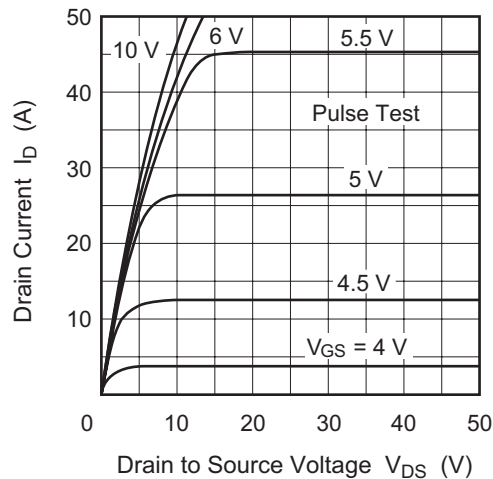
Power vs. Temperature Derating



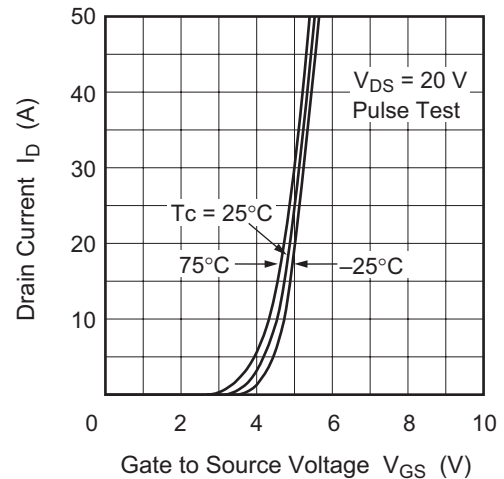
Maximum Safe Operation Area



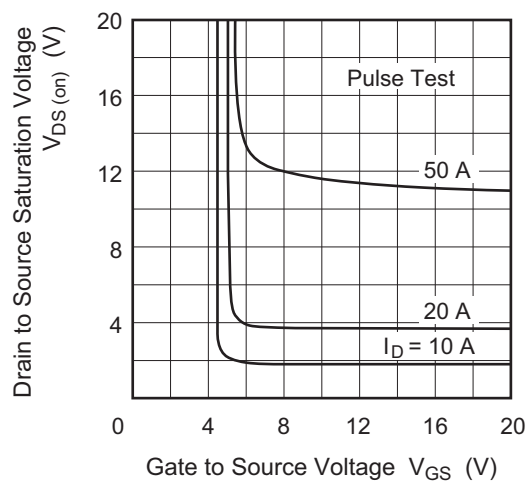
Typical Output Characteristics



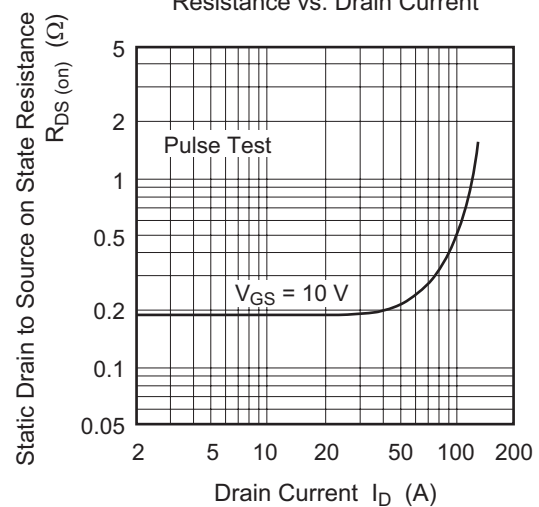
Typical Transfer Characteristics



Drain to Source Saturation Voltage vs. Gate to Source Voltage

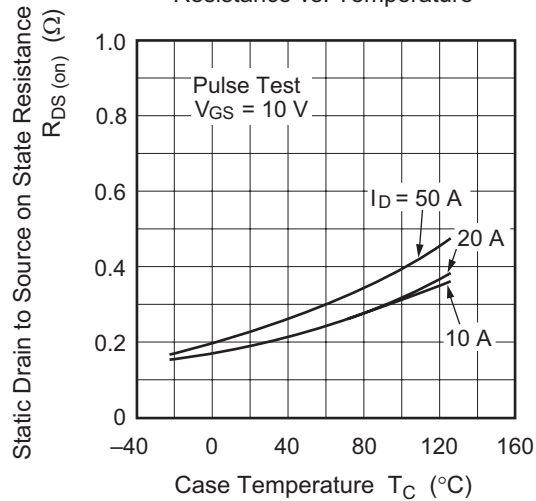


Static Drain to Source on State Resistance vs. Drain Current

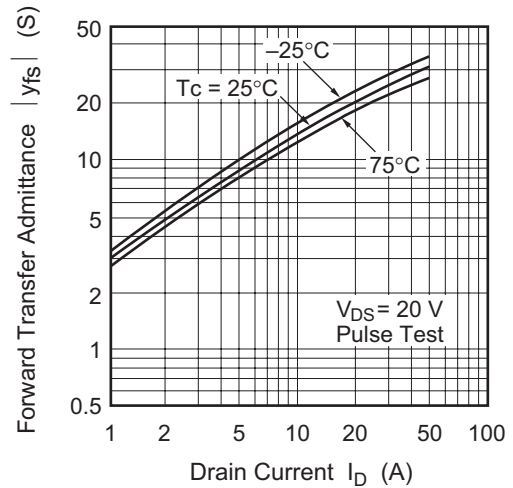


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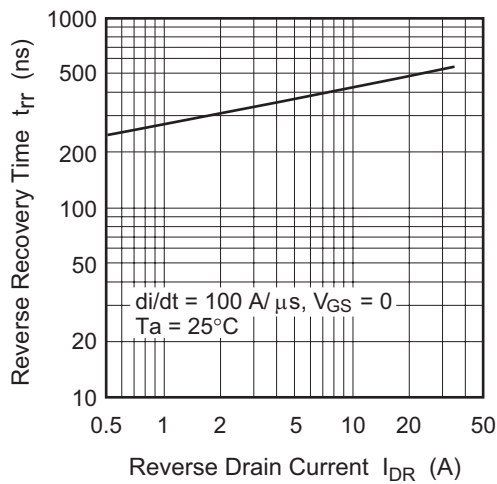
Static Drain to Source on State
Resistance vs. Temperature



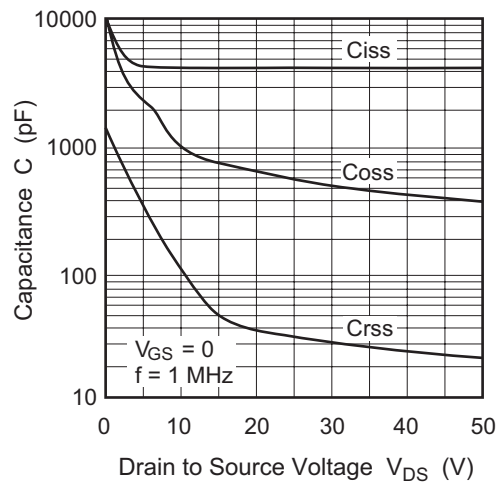
Forward Transfer Admittance
vs. Drain Current



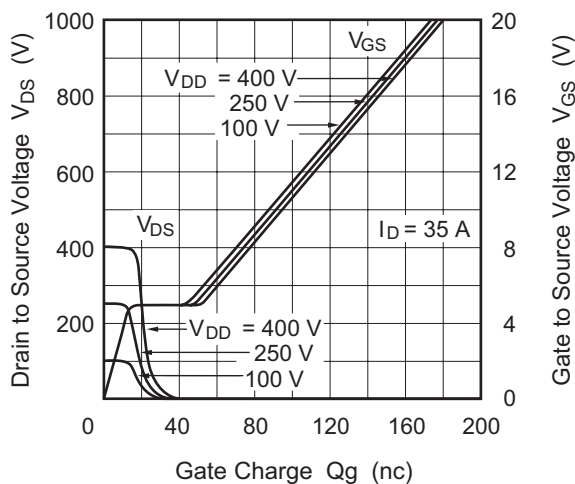
Body to Drain Diode Reverse
Recovery Time



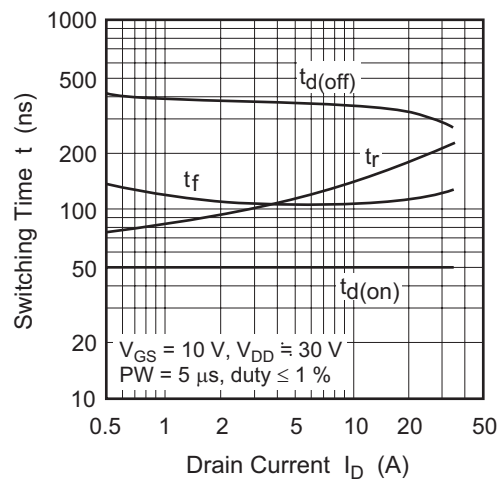
Typical Capacitance vs.
Drain to Source Voltage

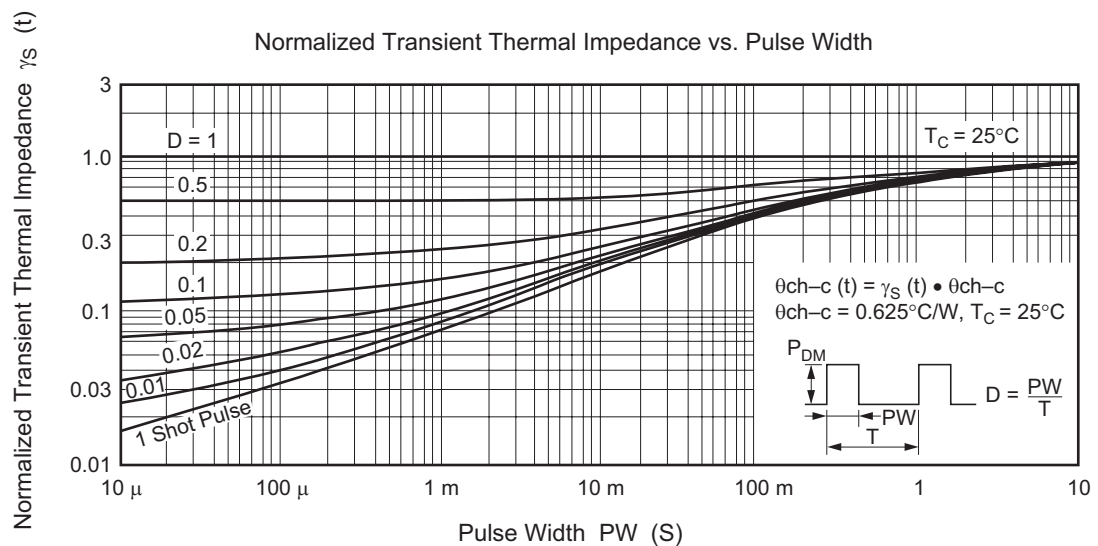
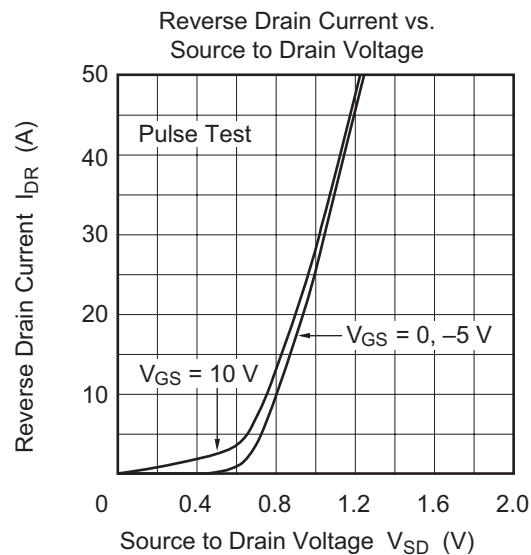


Dynamic Input Characteristics

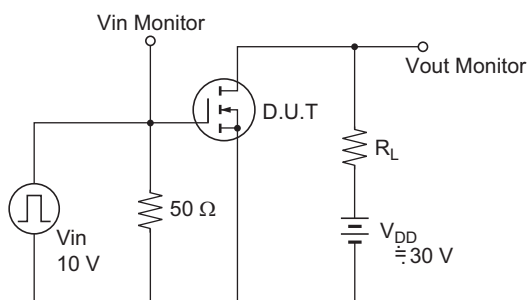


Switching Characteristics

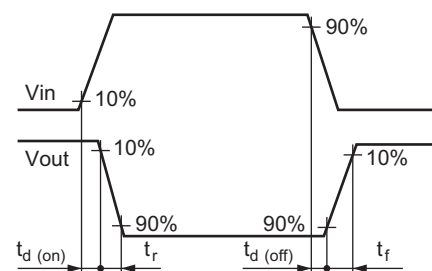


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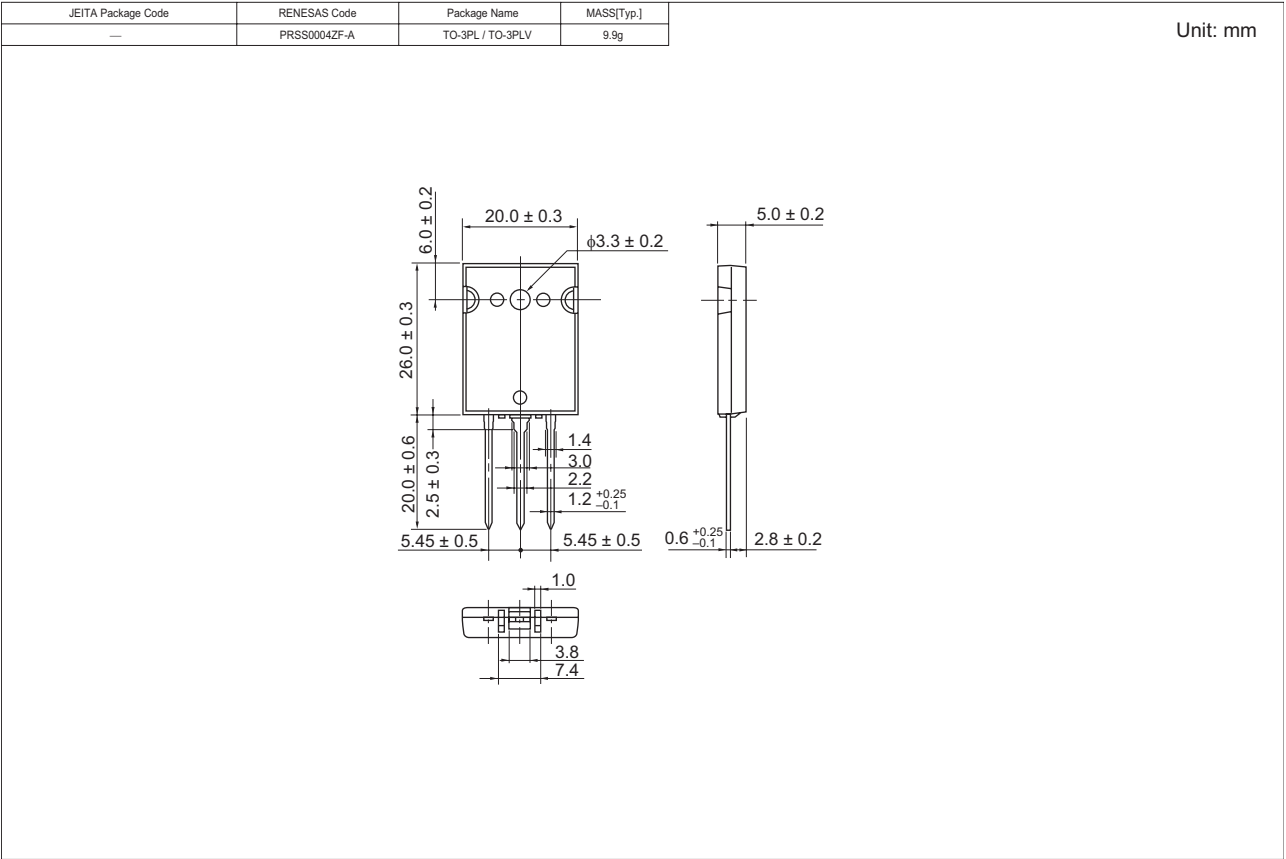
Switching Time Test Circuit



Waveforms



2SK1971-E 供应商



Ordering Information

Part Name	Quantity	Shipping Container
2SK1971-E	500 pcs	Box (Case)

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Renesas Technology America, Inc.

450 Holger Way, San Jose, CA 95134-1368, U.S.A
Tel: <1> (408) 382-7500, Fax: <1> (408) 382-7501

Renesas Technology Europe Limited

Dukes Meadow, Millboard Road, Bourne End, Buckinghamshire, SL8 5FH, U.K.
Tel: <44> (1628) 585-100, Fax: <44> (1628) 585-900

Renesas Technology Hong Kong Ltd.

7th Floor, North Tower, World Finance Centre, Harbour City, 1 Canton Road, Tsimshatsui, Kowloon, Hong Kong
Tel: <852> 2265-6688, Fax: <852> 2730-6071

Renesas Technology Taiwan Co., Ltd.

10th Floor, No.99, Fushing North Road, Taipei, Taiwan
Tel: <886> (2) 2715-2888, Fax: <886> (2) 2713-2999

Renesas Technology (Shanghai) Co., Ltd.

Unit2607 Ruijing Building, No.205 Maoming Road (S), Shanghai 200020, China
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Renesas Technology Singapore Pte. Ltd.

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Tel: <65> 6213-0200, Fax: <65> 6278-8001

Renesas Technology Korea Co., Ltd.

Kukje Center Bldg. 18th Fl., 191, 2-ka, Hangang-ro, Yongsan-ku, Seoul 140-702, Korea
Tel: <82> 2-796-3115, Fax: <82> 2-796-2145

Renesas Technology Malaysia Sdn. Bhd.

Unit 906, Block B, Menara Amcorp, Amcorp Trade Centre, No.18, Jalan Persiaran Barat, 46050 Petaling Jaya, Selangor Darul Ehsan, Malaysia
Tel: <603> 7955-9390, Fax: <603> 7955-9510